

4-19-07

Docket No.: MICRON.003C1
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CPA/Gau 2823



REQUEST FORM FOR CONTINUED PROSECUTION APPLICATION (CPA) UNDER 37 CFR 1.53(d)

Assistant Commissioner for Patents
Box CPA
Washington, D.C. 20231

This is a Request for filing a continuation application under 37 CFR 1.53(d) as a Continued Prosecution Application (CPA) of prior Application No. 09/037,945, filed on March 10, 1998, entitled STREAMLINED FIELD ISOLATION PROCESS, by inventors: Pierre C. Fazan, Viju K. Mathews, Nanseng Jeng

- A 1-month extension for responding to the PTO communication mailed March 27, 2000, in the prior application is hereby requested.

Time Extension Fee:

One Month (\$110)

- A preliminary amendment is enclosed.

The filing fee is calculated on the basis of the claims existing in the prior application as amended above.

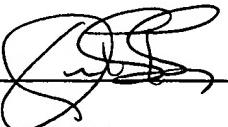
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FOR	NUMBER FILED	NUMBER EXTRA	RATE	FEE
Total Claims	11 - 20 =	0 ×	\$18	\$0
Independent Claims	4 - 3 =	1 ×	\$78	\$78
04/20/2000 STEFERRA 00000035 09037945		BASIC FEE	+ \$690	
G1 FC:102 02 FC:131 03 FC:115	78.00 0P 690.00 0P 110.00 0P			
		TOTAL OF ABOVE CALCULATIONS		\$768
Time Extension Fee				\$110
		TOTAL		\$878

- The power of attorney in the prior application is to the law firm of Knobbe, Martens, Olson & Bear, LLP (Customer No. 20,995).
- A check in the amount of \$878 is enclosed.
- The Commissioner is hereby authorized to charge any additional fees under 37 CFR 1.16 and 1.17 which may be required, now or in the future, or credit any overpayment to Deposit Account No. 11-1410. A duplicate copy of this sheet is enclosed.
- Return prepaid postcard.

Address all future communications to Customer No. 20,995.

Date: April 17, 2000

Signature: 
James B. Bear
Registration No. 25,221
Attorney of Record

INTELLECTUAL PROPERTY LAW

KNOBBE, MARTENS, OLSON & BEAR

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#12/D
4/25/00
PATENT
Murphy

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Fazan et al.
Appl. No. : 09/037,945
Filed : March 10, 1998
For : STREAMLINED FIELD ISOLATION PROCESS
Examiner : George Fourson

) Group Art Unit 2823
)
) I hereby certify that this correspondence and all
) marked attachments are being deposited with
) the United States Postal Service as first-class
) mail in an envelope addressed to: Assistant
) Commissioner for Patents, Washington, D.C.
) 20231, on
)
April 17, 2000
(Date)
James B. Bear, Reg. No. 25,221

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

This is a response to the Office Action mailed on March 27, 2000, in which all of the pending claims were finally rejected. This Preliminary Amendment amends all of the pending claims to clarify the claimed process in a manner which avoids the prior art without altering the principal focus of the claims.

In the Claims:

D1 1. (Thrice Amended) A process of forming an integrated circuit, comprising:
growing a silicon dioxide field isolation region on a semiconductor wafer
without forming silicon nitride inclusions in said field isolation region exclusively by means
of a hydrogen-free oxidant at a pressure less than about 30 atm; and forming a gate oxide
without a prior sacrificial oxidation.

D2 5 & 5. (Thrice Amended) A field isolation region among integrated circuit devices on a
semiconductor substrate formed by a process comprising:
avoiding the formation of silicon nitride inclusions in the field isolation region by
exposing a field region of the semiconductor substrate to a hydrogen-free oxidizing ambient
at a pressure between about 5 atm and 30 atm.

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